

L Number	Hits	Search Text	DB	Time stamp
6	6949	((sensor) near (piezoelectric or piezo-electric or piezo))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:14
7	1243	(((sensor) near (piezoelectric or piezo-electric or piezo))) and displacement	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 16:39
8	4	(((sensor) near (piezoelectric or piezo-electric or piezo))) and (micrometer near displacement)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 16:40
9	33	(((sensor) near (piezoelectric or piezo-electric or piezo))) and (small near displacement)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 16:41
10	4826	(strain near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:21
11	703	((strain near sensor)) and (micro micron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:17
12	8	((strain near sensor)) near (micro micron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:15
13	2	((strain near sensor)) and ((micro micron) near meter)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:18
14	5	((strain near sensor)) and ((micrometer micron) near (displace displacement))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:22
15	28853	(strain near gauge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:50

16	19	((strain near gauge)) and ((micrometer micron) near (displace displacement))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:56
17	5220	(measurement) near (displace displacement)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:24
18	31574	(strain near (sensor gauge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:55
19	352	((measurement) near (displace displacement)) and ((strain near (sensor gauge)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:50
20	4004	(strain near tensile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:50
21	23	((measurement) near (displace displacement)) and ((strain near tensile))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:55
22	35223	(strain near (sensor gauge tensile))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:55
23	366	((measurement) near (displace displacement)) and ((strain near (sensor gauge tensile)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:55
24	8	((((measurement) near (displace displacement)) and ((strain near (sensor gauge tensile)))) and ((millimeter micrometer micron) near (displace displacement)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 17:57
25	36	((((measurement) near (displace displacement)) and ((strain near (sensor gauge tensile)))) and (high near sensitivity))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 18:25

26	376	((sens r) near (piezoelectric r piezo-electric or piezo)) and (high near sensitivity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 18:25
27	82	((((sensor) near (piezoelectric r piezo-electric or piezo)) and (high near sensitivity)) and (micrometer millimeter micron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 18:26
28	7	(((((sensor) near (piezoelectric or piezo-electric or piezo)) and (high near sensitivity)) and (micrometer millimeter micron)) and ((tensile force forced) near (gauge probe strain sensor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 18:27
-	1	chun-keng near hsu	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:36
-	0	tin-hau near kuo	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:36
-	1	chun-chih near lin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:36
-	2	chao-lin near lee	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:37
-	432	wafer near blade	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:15
-	1128713	sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 13:30
-	3798	sensor near strain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:38

-	787	(sensor near strain) and (piezoelectric or piezo-electric or piezo)	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:39
-	73	(sensor near strain) near (piezoelectric or piezo-electric or piezo)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:39
-	0	(wafer near blade) and ((sensor near strain) and (piezoelectric or piezo-electric or piezo))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:39
-	134	(wafer near blade) and sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:39
-	10	((wafer near blade) and sensor) and (piezoelectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:15
-	7	("4610475" "4642438" "4667997" "5100502" "5438419" "5511931" "5641264").PN.	USPAT	2002/11/04 11:11
-	3	"6113165"	USPAT	2002/11/04 11:11
-	21	("4040736" "4093378" "5044752" "5103367" "5173832" "5400209" "5436790" "5444342" "5444597" "5445486" "5556147" "5645391" "5669752" "5841515" "5842491" "5863170" "5867359" "5872694" "5885355" "5903123" "5948986").PN.	USPAT	2002/11/04 11:11
-	4471	wafer near chuck	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:15
-	170	(wafer near chuck) and (piezoelectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:15
-	97	((wafer near chuck) and (piezoelectric)) and sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:16

-	77	((wafer near chuck) and (piezoelectric)) and sensor) and (alarm signal)	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 13:23
-	3	((wafer near chuck) and (piez electric)) and sensor) and (alarm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 13:24
-	134	(wafer near blade) and sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 13:30
-	7	((wafer near blade) and sensor) and alarm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 13:30
-	5358	strain near gage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:56
-	878	(strain near gage) and (wafer semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:56
-	1424	(strain near (sensor or gage)) and (wafer semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:57
-	68	(strain near (sensor or gage)) and (wafer semiconductor) and blade	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 14:58
-	2	("6494882").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 12:45
-	28565	strain near (sensor gauge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 12:46

	605	(wafer semiconductor) near blade	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 12:46
	465244	thin same film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 12:46
	4	(strain near (sensor gauge)) and ((wafer semiconductor) near blade)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 12:48
	5807	piezoelectric near (sensor sensing sensitive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 12:49
	584	(strain near (sensor gauge)) and (piezoelectric near (sensor sensing sensitive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/12 12:50
	5	("4502857" "5043111" "5174933" "5528452" "6294113").PN.	USPAT	2003/08/12 13:31
	145	(73/767).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 13:13
	17035	sensitivity and 73/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 13:16
	468	(sensitivity and 73/\$.ccls.) and (strain near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 13:15
	162268	73/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 15:56
	4339	strain near sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 13:15

-	975	73/\$.ccls. and (strain near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 13:15
-	468	sensitivity and (73/\$.ccls. and (strain near sensor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 13:42
-	18832	(touch contact) near sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 16:06
-	46	(73/\$.ccls. and (strain near sensor)) and ((touch contact) near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 13:43
-	928	((touch contact) near sensor) and micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 15:56
-	10	(strain near sensor) and (((touch contact) near sensor) and micron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 13:52
-	77270	414/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 16:06
-	22990	(strain touch contact) near sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 15:57
-	220	414/\$.ccls. and ((strain touch contact) near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 16:11
-	5	(414/\$.ccls. and ((strain touch contact) near sensor)) and micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 15:58

-	12	("4449885" "4520421" "4565601" "4743570" "4892451" "4911597" "4962441" "4999507" "5007981" "5113992" "5258047" "5315473").PN.	USPAT	2003/08/25 16:03
-	36806	294/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 16:06
-	51	294/\$.ccls. and ((strain touch contact) near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 16:10
-	5822	wafer near (blade chuck gripper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 16:11
-	49	(wafer near (blade chuck gripper)) and ((strain touch contact) near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 16:11
-	29618	strain near (sensor gauge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:33
-	5606	sensitivity same micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:33
-	94	(strain near (sensor gauge)) and (sensitivity same micron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:38
-	116	(73/768).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:56
-	524	piezo-electric near sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:48

-	60	(strain near (sensor gauge)) and (piezo-electric near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:48
-	1	((strain near (sensor gauge)) and (piezo-electric near sensor)) and micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:43
-	5260	piezoelectric near sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:48
-	578	(strain near (sensor gauge)) and (piezoelectric near sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:48
-	143	((strain near (sensor gauge)) and (piezoelectric near sensor)) and (semiconductor wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 17:49
-	145	(73/769).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 18:17
-	60	(73/770).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/25 18:17
-	622	(semiconductor wafer) near blade	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:42
-	1399972	(semiconductor wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:42
-	110214	((semiconductor wafer)) and sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:43

	7687	((semiconductor wafer)) and sensor) and strain	USPAT; US-P PUB; EP ; JPO; DERWENT; IBM_TDB	2003/10/17 14:43
	1985	(((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:44
	7	(((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 294/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 14:54
	35	("Re28663" "1315581" "3353860" "3370213" "3491520" "3625378" "3827437" "4130314" "4540211" "4544193" "4552397" "4565400" "4579380" "4590673" "4610475" "4667997" "4671553" "4694230" "4696501" "4699414" "4723806" "4735451" "4796357" "4808898" "4813732" "4816730" "4819978" "4828309" "4872803" "4898416" "4955656" "4976484" "5046773" "5080415" "5163804").PN.	USPAT	2003/10/17 14:49
	13	(((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 414/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 15:02
	7	("4610475" "4642438" "4667997" "5100502" "5438419" "5511931" "5641264").PN.	USPAT	2003/10/17 14:59
	50	(((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 29/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 15:14
	10	("4674186" "5266801" "5325081" "5345815" "5386720" "5400647" "5468959" "5469733" "5907095" "6072247").PN.	USPAT	2003/10/17 15:06
	502	(((semiconductor wafer)) and sensor) and strain) and (piezoelectric piezo-electric)) and 73/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 15:15

-	123	(((((semiconductor waf r) and sens r) and strain) and (piezoelectric piezo-electric)) and 73\$.ccls.) and micro	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 15:15
-	10800	piez electric near (layer sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:41
-	622	(wafer semiconductor) near blade	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:40
-	4	(piezoelectric near (layer sensor)) and ((wafer semiconductor) near blade)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:15
-	1399972	(wafer semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:20
-	2089	(piezoelectric near (layer sensor)) and ((wafer semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:20
-	611	((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:21
-	496	((piezoelectric near (layer sensor)) and ((wafer semiconductor))) and (micron micrometer)) and thin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:21
-	8680	(wafer semiconductor) near (grip gripper handler holder blade)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:41
-	14601	piezoelectric near (film layer sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:42

-	5501	(piezoelectric near (film layer sensor)) and thin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:45
-	24	((wafer semiconductor) near (grip gripper handler holder blade)) and ((piezoelectric near (film layer sensor)) and thin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:45
-	27	((wafer semiconductor) near (grip gripper handler holder blade)) and (piezoelectric near (film layer sensor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:45
-	1256	((piezoelectric near (film layer sensor)) and thin) and (micron micrometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:46
-	663	((((piezoelectric near (film layer sensor)) and thin) and (micron micrometer)) and sensor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:46
-	663	(((piezoelectric near (film layer sensor)) and thin) and (micron micrometer)) and sensor) and thin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:47
-	487	(((piezoelectric near (film layer sensor)) and thin) and (micron micrometer)) and sensor) and (thin near (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 18:59
-	2	("6469421").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 18:59
-	4	("5681410" "6103072" "6284434" "6332254").PN.	USPAT	2003/10/17 18:59